

## **NCE N-Channel Super Trench Power MOSFET**

### **Description**

The NCEP40T15AGU uses Super Trench technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS}(\text{ON})}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification

## **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

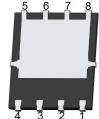
#### **General Features**

- V<sub>DS</sub> =40V,I<sub>D</sub> =150A  $R_{DS(ON)}$ =1.15m $\Omega$ , typical@  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 150°C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

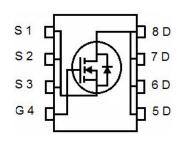
### DFN5X6







**Top View Bottom View** 



**Schematic Diagram** 

## **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P40T15AGU	NCEP40T15AGU	DFN5X6-8L	-	-	-

### Absolute Maximum Ratings (T<sub>c</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	150	Α
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	106	А
Pulsed Drain Current	I <sub>DM</sub>	600	Α
Maximum Power Dissipation	P <sub>D</sub>	135	W
Derating factor		1.1	W/℃
Single pulse avalanche energy (Note 1)	Eas	1344	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	°C

### **Thermal Characteristic**

Thermal Resistance,Junction-to-Case	R <sub>eJC</sub>	0.93	°C/W
,			1

# NCEP40T15AGU

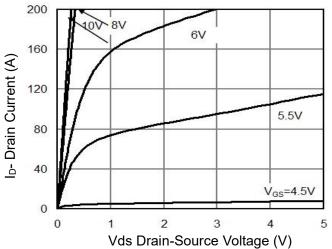
## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	,			•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	40		-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics	·					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =75A	-	1.15	1.45	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =75A		80	-	S
Dynamic Characteristics			·			
Input Capacitance	C <sub>lss</sub>	\/ 00\/\/ 0\/	-	4135	-	PF
Output Capacitance	Coss		-	2110	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	120	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	9	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =20 $V$ , $I_D$ =75 $A$	-	6	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V <sub>GS</sub> =10V,R <sub>G</sub> =1.6Ω	-	42	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	Qg	\/ 00\/ L 75A	-	62	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DD</sub> =20V,I <sub>D</sub> =75A	-	19.7	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	14.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =75A	-		1.2	V
Diode Forward Current	Is		-	-	150	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub>	-		30	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/μs	-		110	nC

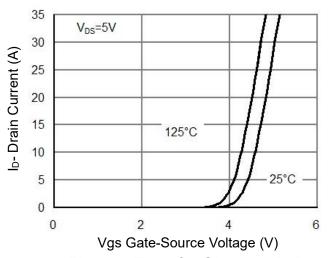
### Notes:

- 1. EAS condition : Tj=25  $^{\circ}\text{C}$  ,VDD=20V,VG=10V,L=0.5mH,Rg=25 $\Omega$
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=150° C. The SOA curve provides a single pulse rating.





**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

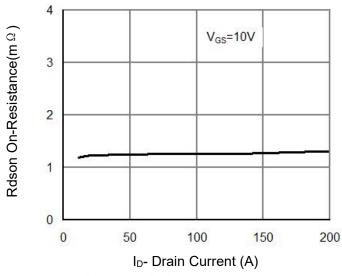


Figure 3 Rdson- Drain Current

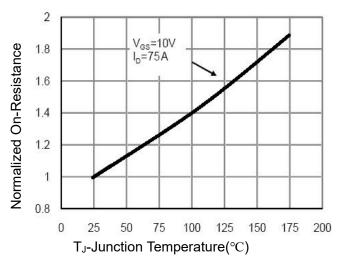


Figure 4 Rdson-JunctionTemperature

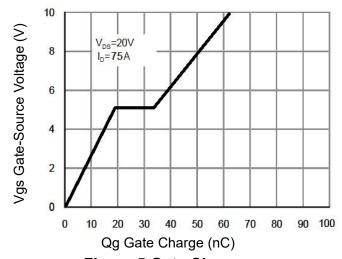
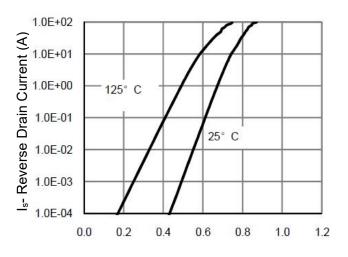


Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)
Figure 6 Source- Drain Diode Forward

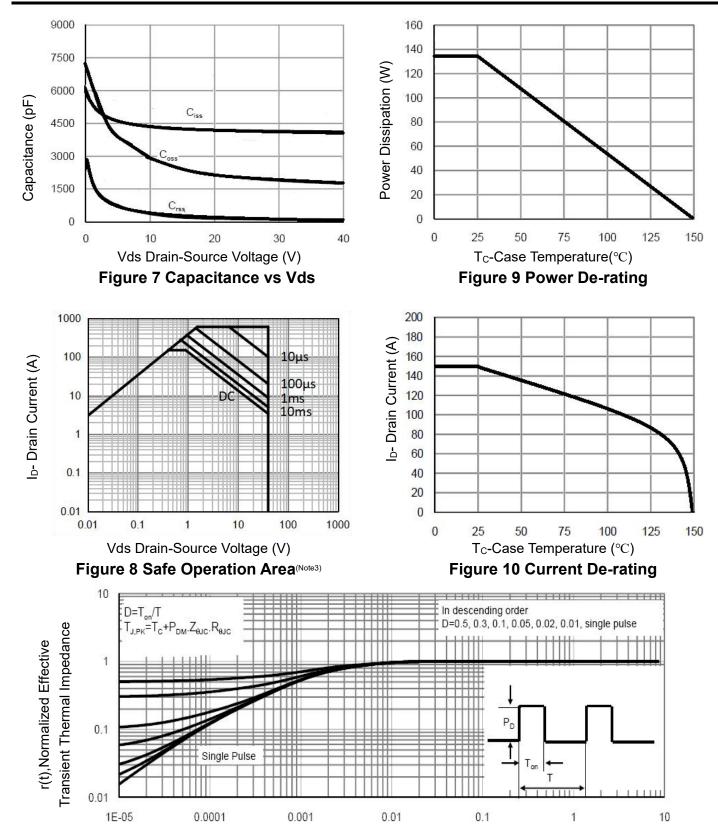
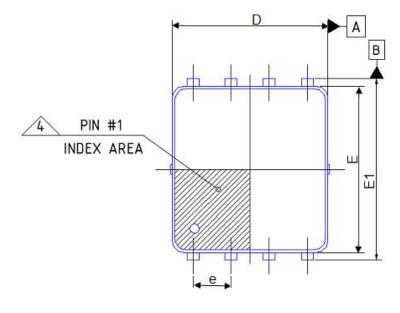


Figure 11 Normalized Maximum Transient Thermal Impedance

Square Wave Pluse Duration(sec)

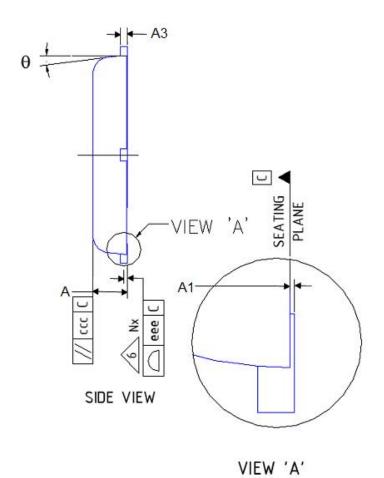
# DFN5X6-8L(f) Package Information



dada M Nxb S(N) S

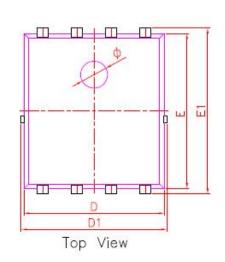
TOP VIEW

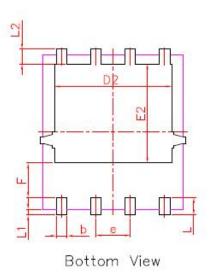
BOTTOM VIEW

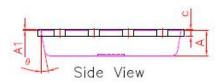


8	D	limension	Table	
Thickness Symbol	V		NOTE	
Jupol 2	MINIMUM	NOMINAL	MAXIMUM	
Α	0.85	0.95	1.00	
A1	0.00		0.05	
A3		0.2 Ref		
b	0.30	0.40	0.50	
D	5.10	5.20	5.30	
E	5.45	5.55	5.65	
е		1.27 BSC		
D1	4.25	4.35	4.45	
E1	5.95	6.05	6.15	
E2	3.525	3.625	3.725	
E3	1.175	1.275	1.375	
L	0.45	0.55	0.65	
L1	0		0.15	
L2		0.68 REF		
θ	0°		10°	
aaa		0.05		
bbb		0.10		
ССС	,	0.10		
ddd	0.05 0.08			
eee				
N	8			
ND	4			
NOTES	NOTES 1,2			

# DFN5X6-8L(E) Package Information

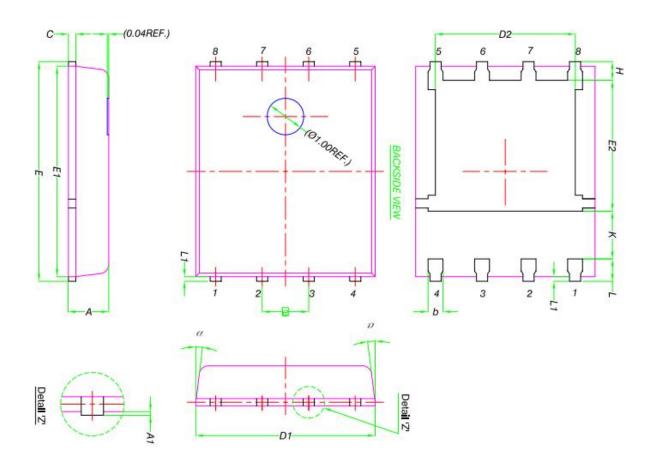




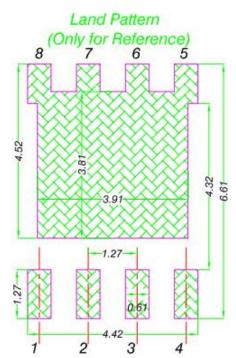


DIM.	MIN.	NOM.	MAX.	
Α	0.90	0.95	1.00	
A1	0.00	0.02	0.05	
b	0.35	0.40	0.50	
С	0.20	0.25	0.30	
D	5.10	5.20	5.30	
D1	5.10	5.40	5.50	
D2	4.25	4.35	4.45	
е		1.27 BSC		
Ε	5.70	5.75	5.80	
E1	6.00	6.15	6.30	
E2	3.57	3.67	3.77	
F	1.18	1.28	1.38	
L	0.55	0.65	0.75	
L1	0.15	0.20	0.25	
L2	0.45	0.55	0.65	
Ø	0.90	1.00	1.10	
Θ	8.	10*	12*	

# DFN5X6-8L (G) Package Information



	MILLIMETERS				
DIM.	MIN.	NOM.	MAX.		
Α	0.90	1.00	1.10		
A1	0	-	0.05		
b	0.33	0.41	0.51		
С	0.20	0.25	0.30		
D1	4.80	4.90	5.00		
D2	3.61	3.81	3.96		
Ε	5.90	6.00	6.10		
E1	5.70	5.75	5.80		
E2	3.38	3.58	3.78		
е	1.27 BSC				
Н	0.41	0.51	0.61		
K	1.10	-	-		
L	0.51	0.61	0.71		
L1	0.06	0.13	0.20		
α	0°	15	12°		



# NCEP40T15AGU

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